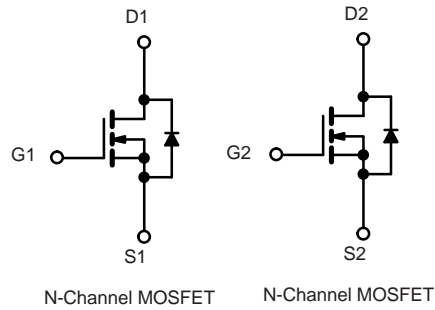


## Dual N-Channel 100V (D-S) MOSFET

PRODUCT SUMMARY		
V <sub>DS</sub> (V)	R <sub>DS(on)</sub> (Ω)	I <sub>D</sub> (A) <sup>a</sup>
100	0.018at V <sub>GS</sub> = 10 V	35
	0.022at V <sub>GS</sub> = 4.5 V	36

### FEATURES

- 175 °C Junction Temperature
- Trench technology Power MOSFET
- Material categorization:



ABSOLUTE MAXIMUM RATINGS (T <sub>C</sub> = 25 °C, unless otherwise noted)				
Parameter		Symbol	Limit	Unit
Gate-Source Voltage		V <sub>GS</sub>	±20	V
Continuous Drain Current (T <sub>J</sub> = 175 °C) <sup>b</sup>	T <sub>C</sub> = 25 °C	I <sub>D</sub>	35	A
	T <sub>C</sub> = 100 °C		20 <sup>a</sup>	
Pulsed Drain Current		I <sub>DM</sub>	105	
Continuous Source Current (Diode Conduction)		I <sub>S</sub>	76 <sup>a</sup>	
Avalanche Current		I <sub>AS</sub>	82	
Single Avalanche Energy (Duty Cycle ≤ 1 %)	L = 0.1 mH	E <sub>AS</sub>	110	mJ
Maximum Power Dissipation	T <sub>C</sub> = 25 °C	P <sub>D</sub>	136	W
	T <sub>A</sub> = 25 °C		3 <sup>b</sup> , 8.3 <sup>b, c</sup>	
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	- 55 to 175	°C

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient <sup>a</sup>	t ≤ 10 sec	R <sub>thJA</sub>	15	18	°C/W
	Steady State		60	50	
Maximum Junction-to-Case		R <sub>thJC</sub>	0.85	1.1	

Notes:

- a. Package limited.
- b. Surface mounted on 1" x 1" FR4 board.
- c. t ≤ 10 s.

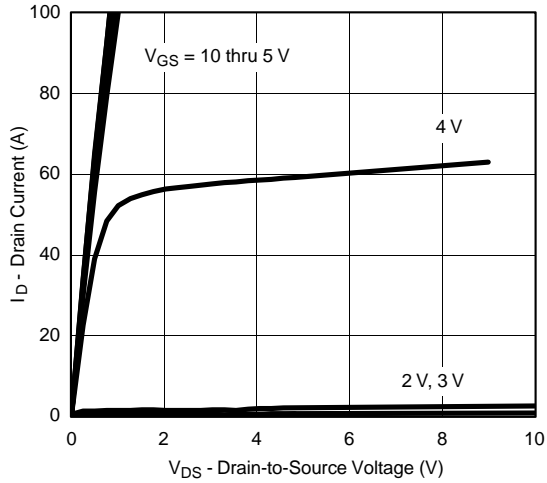
SPECIFICATIONS (T <sub>J</sub> = 25 °C, unless otherwise noted)						
Parameter	Symbol	Test Conditions	Min.	Typ. <sup>a</sup>	Max.	Unit
<b>Static</b>						
Drain-Source Breakdown Voltage	V <sub>DS</sub>	V <sub>GS</sub> = 0 V, I <sub>D</sub> = 250 μA	100			V
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μA	1	2	3	
Gate-Body Leakage	I <sub>GSS</sub>	V <sub>DS</sub> = 0 V, V <sub>GS</sub> = ± 20 V			± 100	nA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = 30V, V <sub>GS</sub> = 0 V			1	μA
		V <sub>DS</sub> = 30V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 125 °C			50	
		V <sub>DS</sub> = 30V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 175 °C			250	
On-State Drain Current <sup>b</sup>	I <sub>D(on)</sub>	V <sub>DS</sub> = 5 V, V <sub>GS</sub> = 10 V	60			A
Drain-Source On-State Resistance <sup>b</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 20 A		0.018		Ω
		V <sub>GS</sub> = 10 V, I <sub>D</sub> = 20 A, T <sub>J</sub> = 125 °C		0.008		
		V <sub>GS</sub> = 10 V, I <sub>D</sub> = 20 A, T <sub>J</sub> = 175 °C		0.010		
		V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 12A		0.022		
Forward Transconductance <sup>b</sup>	g <sub>fs</sub>	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 20 A		60		S
<b>Dynamic</b>						
Input Capacitance	C <sub>iss</sub>	V <sub>GS</sub> = 0 V, V <sub>DS</sub> = 100 V, f = 1 MHz		3900		pF
Output Capacitance	C <sub>oss</sub>			470		
Reverse Transfer Capacitance	C <sub>rss</sub>			225		
Total Gate Charge <sup>c</sup>	Q <sub>g</sub>	V <sub>DS</sub> = 100 V, V <sub>GS</sub> = 10 V, I <sub>D</sub> = 50 A		89	70	nC
Gate-Source Charge <sup>c</sup>	Q <sub>gs</sub>			26		
Gate-Drain Charge <sup>c</sup>	Q <sub>gd</sub>			23		
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>	V <sub>DD</sub> = 100 V, R <sub>L</sub> = 0.6 Ω I <sub>D</sub> ≅ 50 A, V <sub>GEN</sub> = 10 V, R <sub>g</sub> = 2.5 Ω		21	25	ns
Rise Time <sup>c</sup>	t <sub>r</sub>			15	25	
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>			35	50	
Fall Time <sup>c</sup>	t <sub>f</sub>			20	30	
<b>Source-Drain Diode Ratings and Characteristics (T<sub>C</sub> = 25 °C)</b>						
Pulsed Current	I <sub>SM</sub>				105	A
Diode Forward Voltage	V <sub>SD</sub>	I <sub>F</sub> = 20 A, V <sub>GS</sub> = 0 V		1	1.5	V
Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = 20 A, di/dt = 100 A/μs		4	135	ns

Notes:

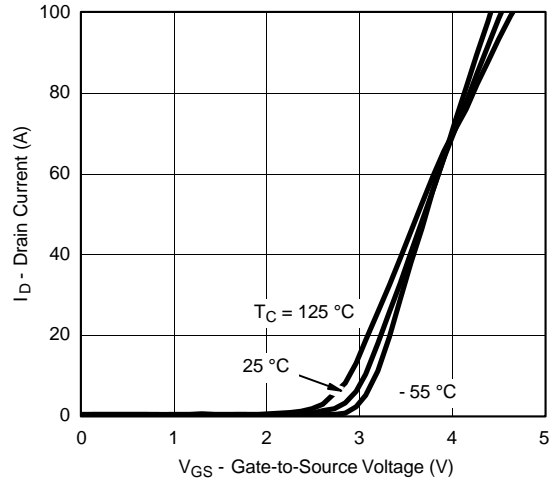
- a. For design aid only; not subject to production testing.
- b. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2 %.
- c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

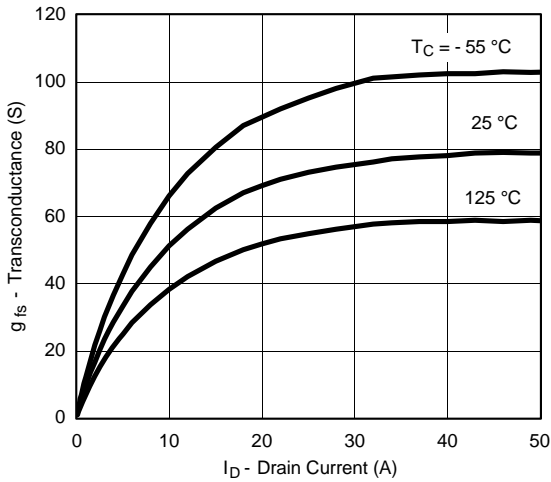
**TYPICAL CHARACTERISTICS** (25 °C unless noted)



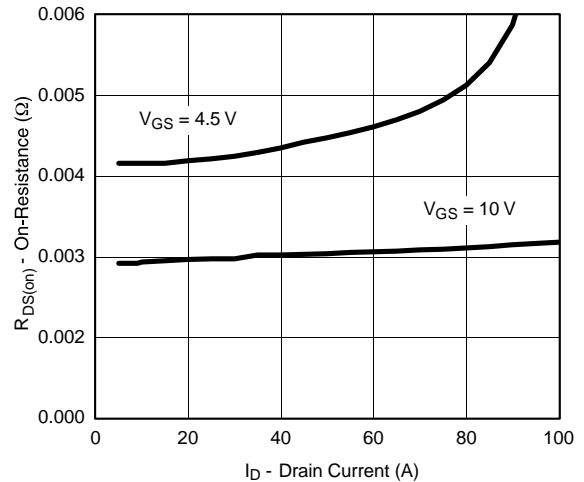
**Output Characteristics**



**Transfer Characteristics**



**Transconductance**



**On-Resistance vs. Drain Current**



**Capacitance**

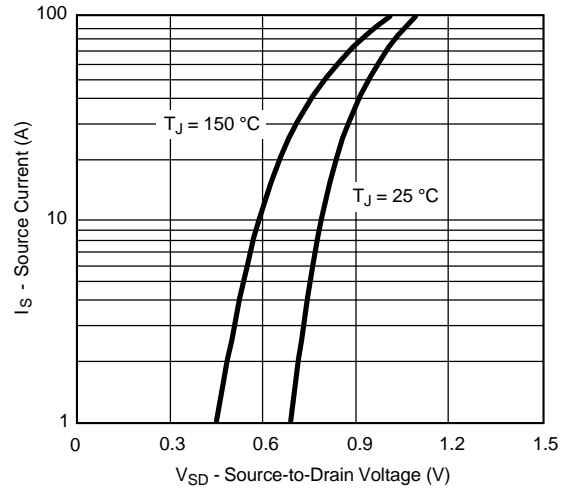


**Gate Charge**

**TYPICAL CHARACTERISTICS** (25 °C unless noted)



**On-Resistance vs. Junction Temperature**

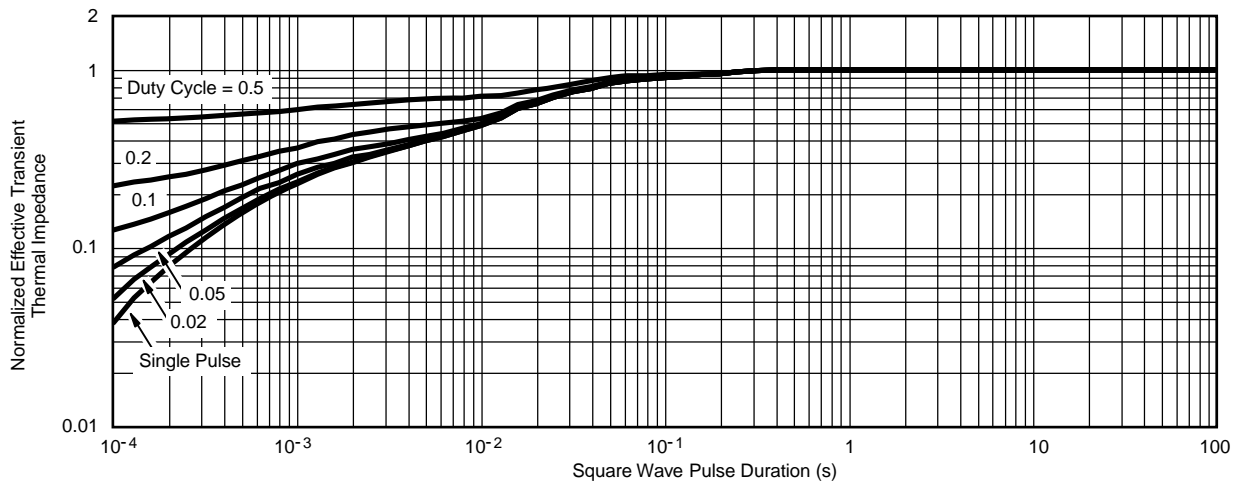
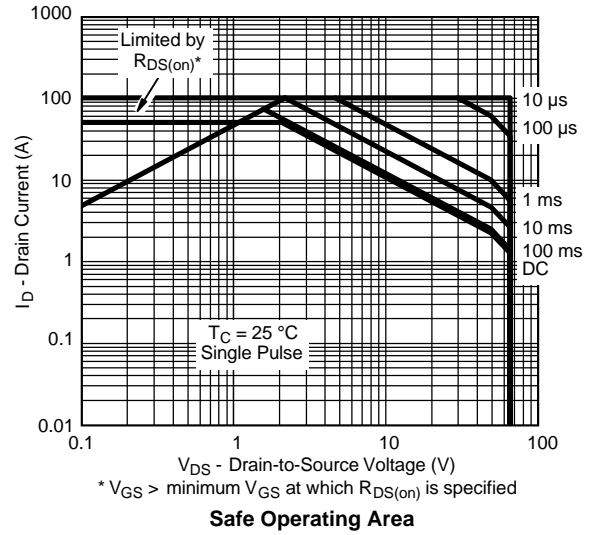


**Source-Drain Diode Forward Voltage**

**THERMAL RATINGS**

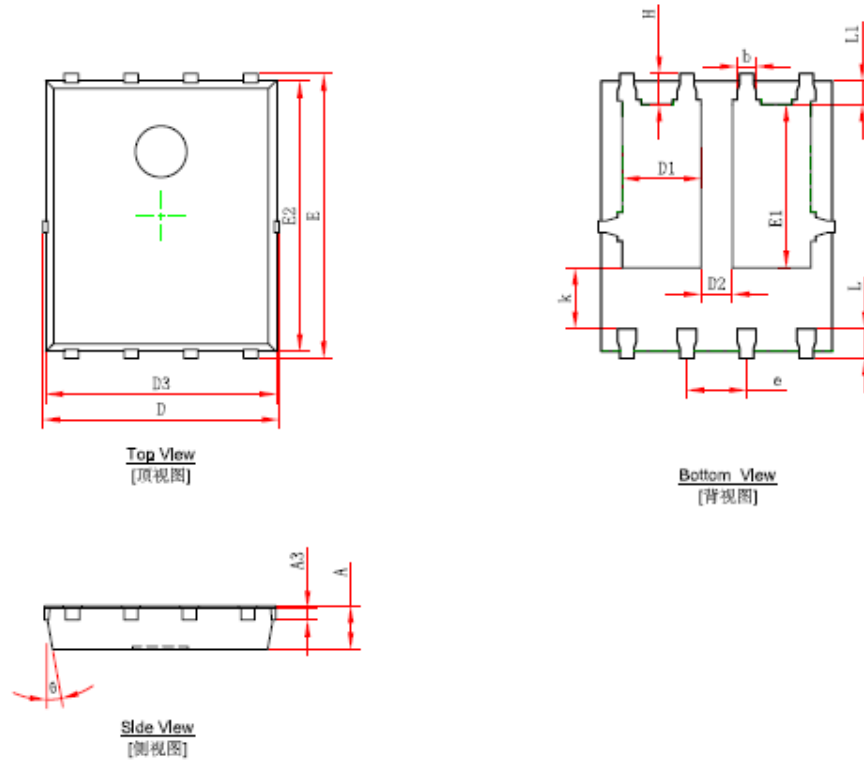


Maximum Drain Current vs. Ambient Temperature



Normalized Thermal Transient Impedance, Junction-to-Case

PDFNWB5×6-8L-A PACKAGE OUTLINE DIMENSIONS



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.000	0.035	0.039
A3	0.254 REF.		0.010REF.	
D	4.944	5.096	0.195	0.201
E	5.974	6.126	0.235	0.241
D1	1.470	1.870	0.058	0.074
D2	0.470	0.870	0.019	0.034
E1	3.375	3.575	0.133	0.141
D3	4.824	4.976	0.190	0.196
E2	5.674	5.826	0.223	0.229
k	1.190	1.390	0.047	0.055
b	0.350	0.450	0.014	0.018
e	1.270TYP.		0.050TYP.	
L	0.559	0.711	0.022	0.028
L1	0.424	0.576	0.017	0.023
H	0.574	0.726	0.023	0.029
θ	10°	12°	10°	12°

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